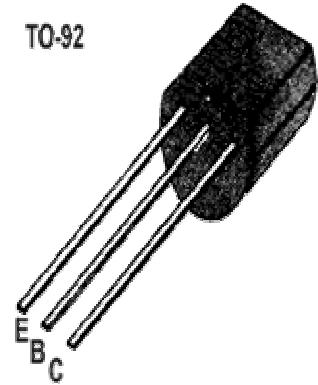


■■ APPLICATION: High Voltage Driver Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-300	V
Collector-emitter voltage	V _{CEO}	-300	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-500	mA
Collector Power Dissipation	P _c	625	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	40				V _{CE} = -10 V, I _c = -10 mA
Collector Cut-off Current	I _{CBO}			0.25	μA	V _{CB} = -200 V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.1	μA	V _{EB} = -3 V, I _c =0
Collector-Base Breakdown Voltage	BV _{CBO}	-300			V	I _c = -0.1 mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-300			V	I _c = -1 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1 mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.5	V	I _c = -20 mA, I _B = -2 mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			-0.9	V	I _c = -20 mA, I _B = -2 mA
Gain bandwidth product	f _r	50			MHz	I _c = -10 mA, V _{CE} = -20 V, f = 100MHz
Common Base Output Capacitance	C _{ob}			6	PF	V _{CB} = -20 V, I _E =0, f = 1MHz

■■ h_{FE} Classification

Classification

h_{FE} >40